

GENERAL DESCRIPTION

The HM2309DR is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

FEATURES

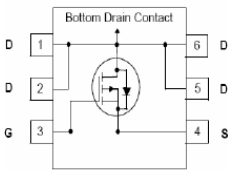
- $R_{DS(ON)} \leq 188m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} \leq 266m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- Capable doing Cu wire bonding

APPLICATIONS

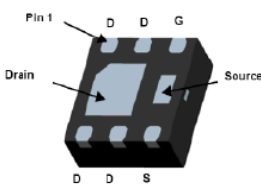
- Power Management
- Portable Equipment
- Battery Powered System
- Load Switch

Absolute Maximum Ratings (TA=25°C Unless Otherwise Noted)

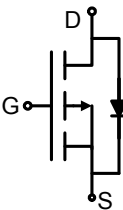
Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V



Pin assignment



DFN2X2-6L bottom view



Schematic diagram

Electrical Characteristics (T_j = 25°C Unless Otherwise Specified)

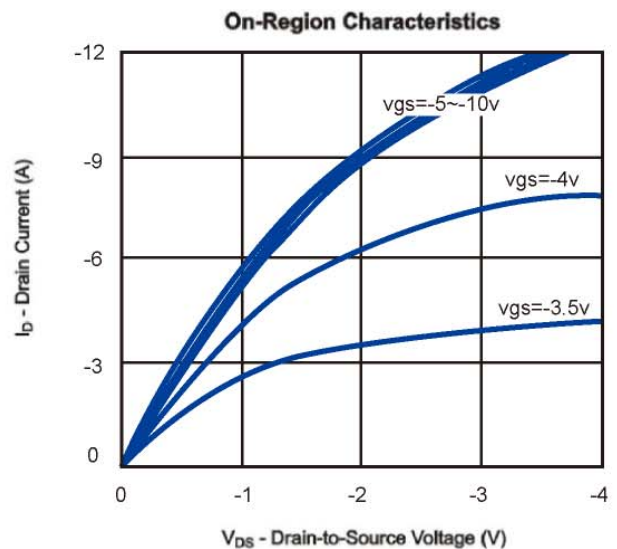
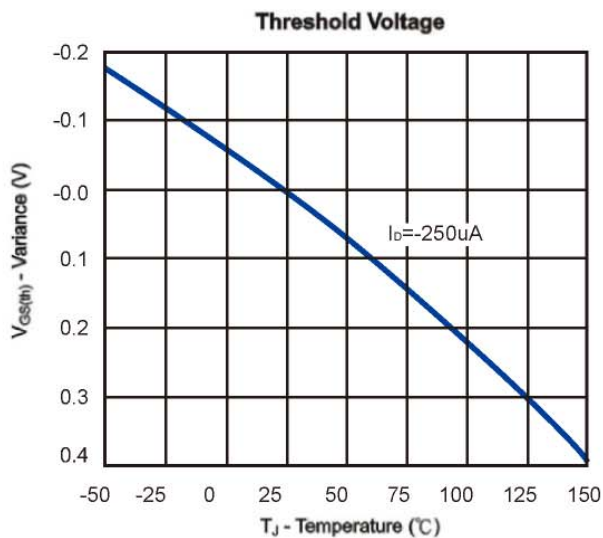
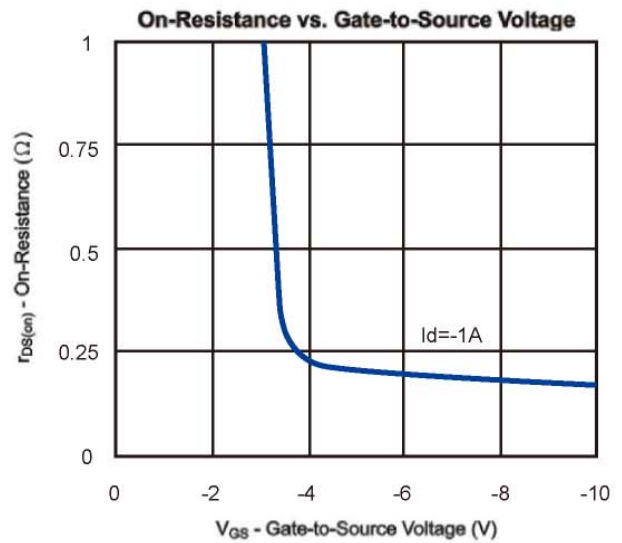
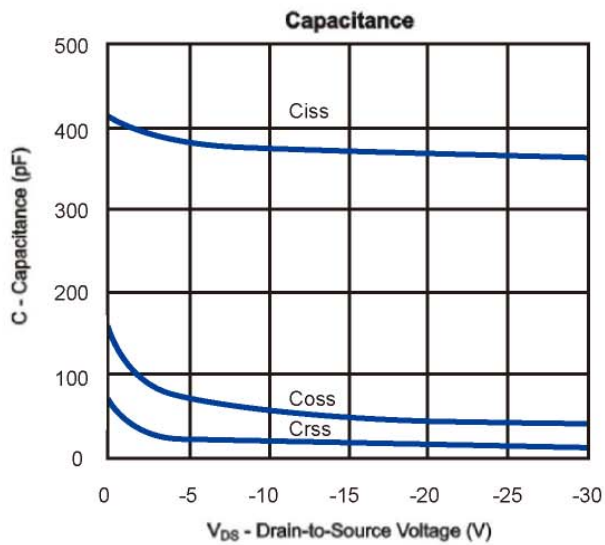
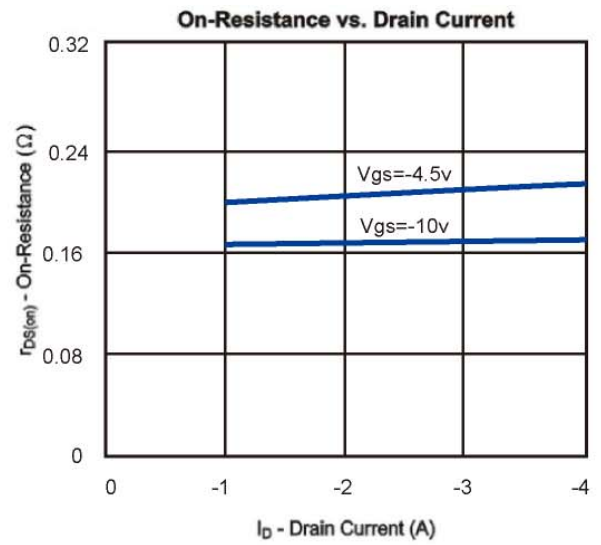
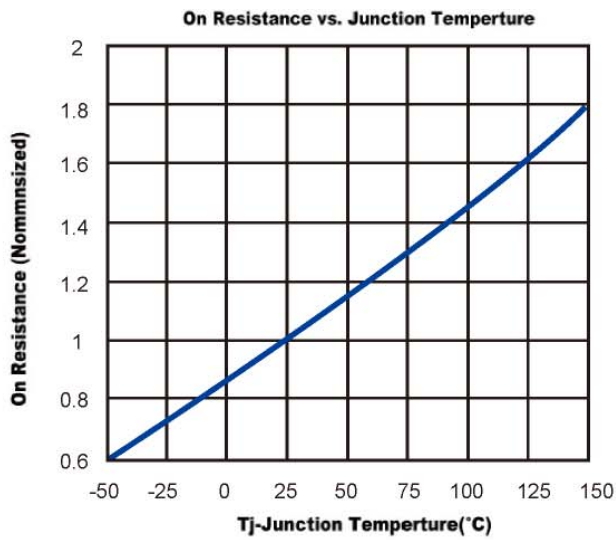
Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μA	-60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μA	-1		-2.5	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V			-10	μA
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} =-10V, I _D = -2.2A			188	mΩ
		V _{GS} =-4.5V, I _D = -1.4A			266	
V _{SD}	Diode Forward Voltage	I _S =-1.2A, V _{GS} =0V			-1.2	V
DYNAMIC						
Q _g	Total Gate Charge	V _{DS} =-48V, V _{GS} =-4.5V, I _D =-1A		6.3		nC
Q _{gs}	Gate-Source Charge			2.3		
Q _{gd}	Gate-Drain Charge			1.8		
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz		9.8		Ω
t _{d(on)}	Turn-On Delay Time	V _{DS} =-30V, R _L =30Ω R _{GEN} =3.3Ω, V _{GS} =-10V I _D =-1A		20		ns
t _r	Turn-On Rise Time			33.1		
t _{d(off)}	Turn-Off Delay Time			5.2		
t _f	Turn-Off Fall Time			3.8		
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz		364		pF
C _{oss}	Output Capacitance			41		
C _{rss}	Reverse Transfer Capacitance			12		

Notes: a. Based on epoxy or solder paste and bond wire Au or Cu 2mil×2(S), Au or Cu 2mil×1 (G) on each die of SOT-23 (SC-59) package.

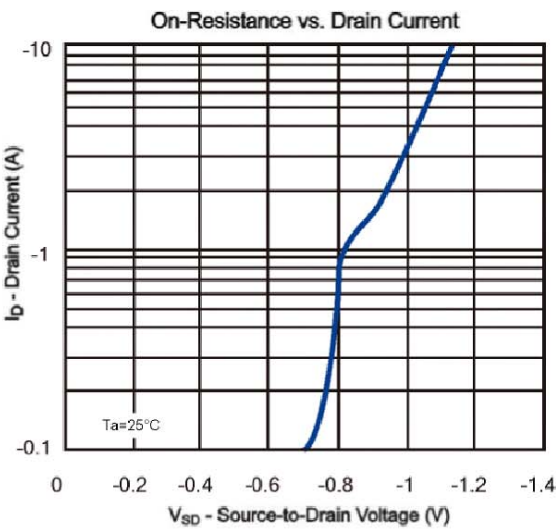
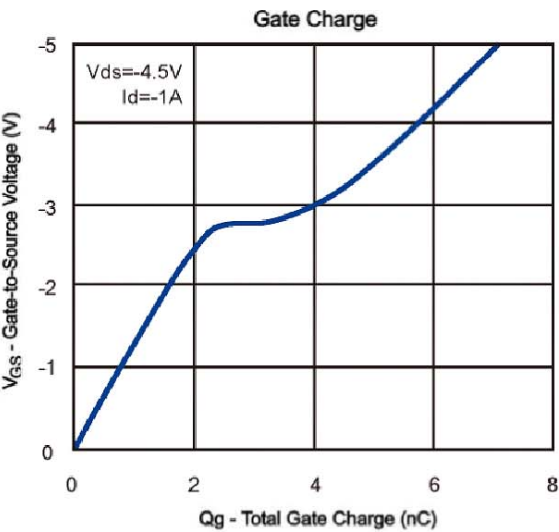
b. Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%.

c. H&M SEMI reserves the right to improve product design, functions and reliability without notice.

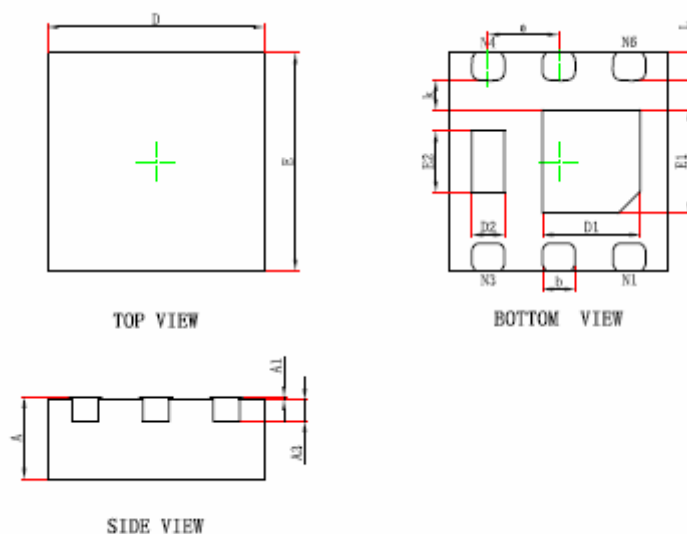
Typical Characteristics (T_J = 25°C Noted)



Typical Characteristics (TJ =25℃ Noted)



DFN2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.